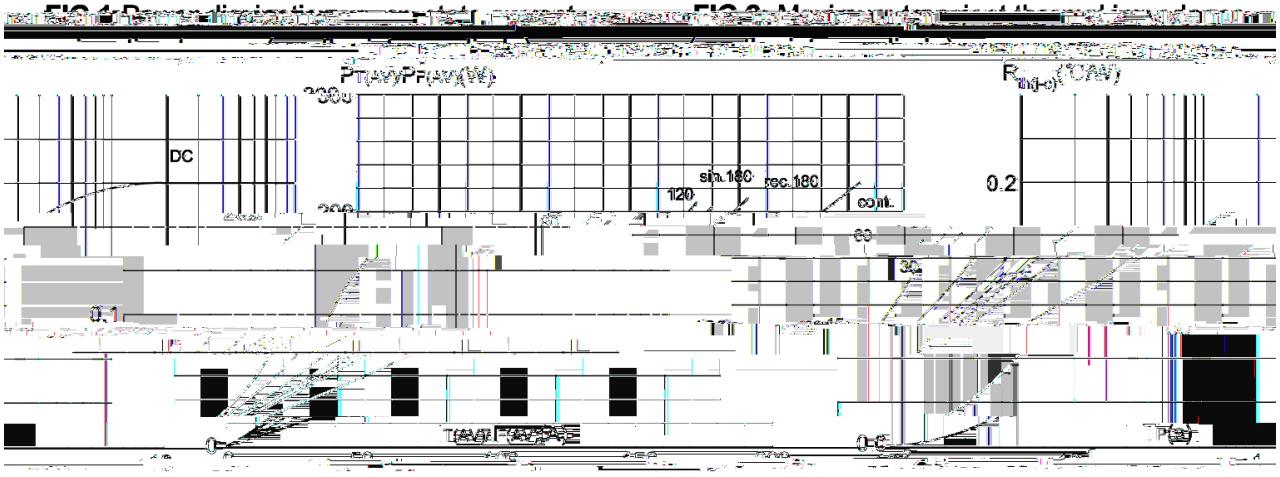
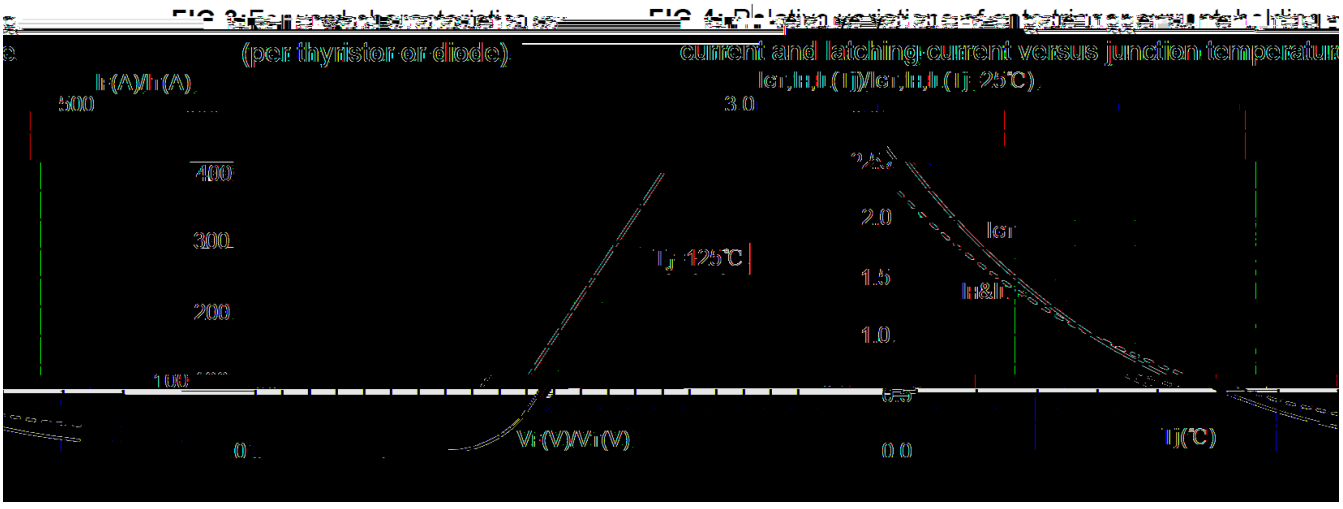
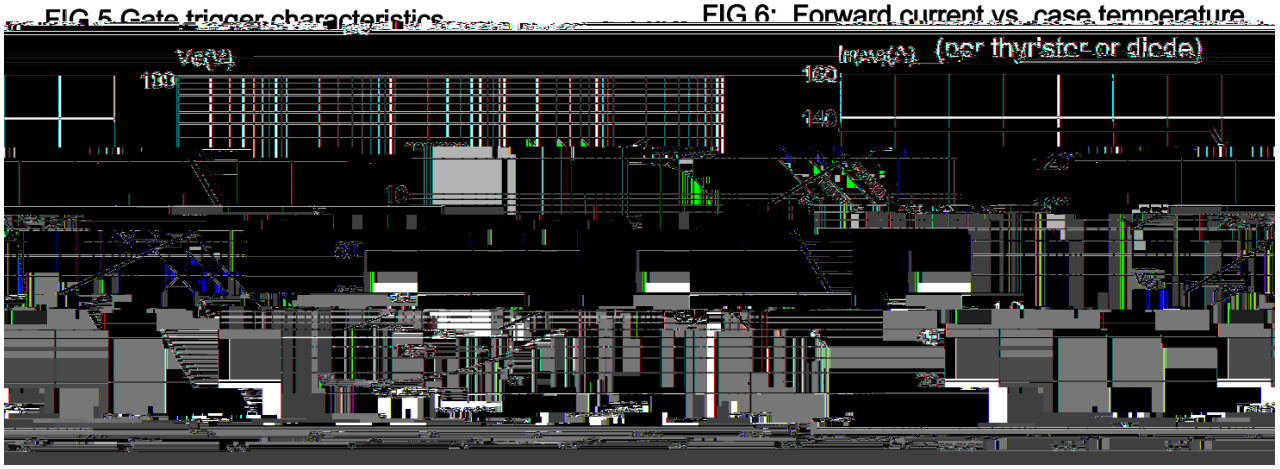
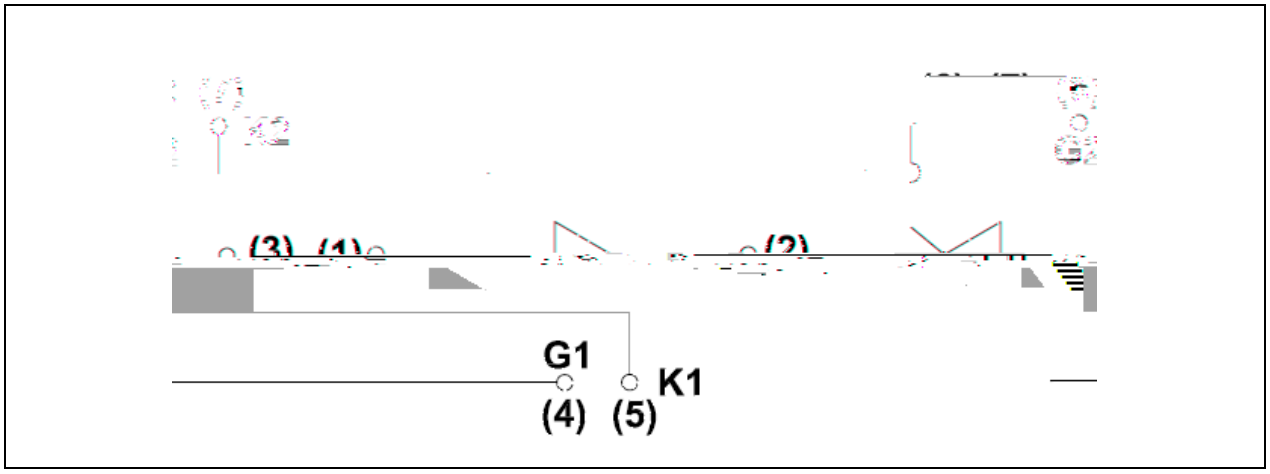
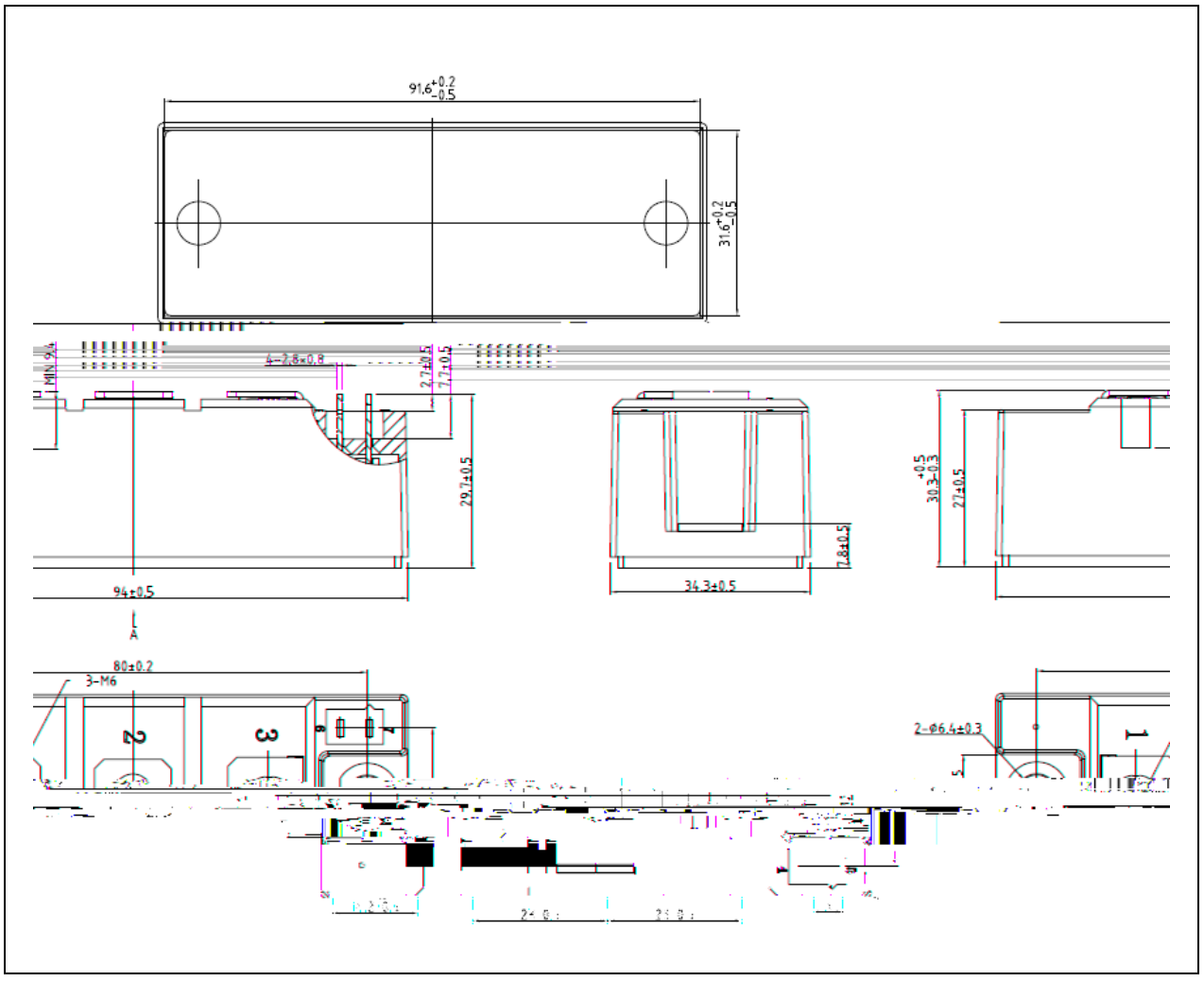



DC
sin.180
rec.180
120
0.2
0.1
0


(per thyristor or diode)
500
400
300
200
100
0
Tj: 125℃
2.5
2.0
1.5
1.0
0.5
0.0
Tj(℃)


Vg(V)
100
10
1
0.1
160
140
120
100
80
60
40
20
0
(per thyristor or diode)


(3)
(1)
(2)
G1
K1
(4)
(5)


91.6+0.2 -0.5
31.6+0.2 -0.5
MIN 9.4
4-2.8×0.8
2.7±0.5
7.7±0.5
29.7±0.5
94±0.5
34.3±0.5
7.8±0.5
30.3+0.5 -0.3
27±0.5
A
80±0.2
3-M6
2-φ6.4±0.3